18-bit Universal Bus Transceivers with 3-state Outputs

HITACHI

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Description

Data flow in each direction is controlled by output enable (OEAB and \overline{OEBA}), latch enable (LEAB and LEBA), and clock (\overline{CLKAB} and \overline{CLKBA}) inputs. For A to B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if \overline{CLKAB} is held at a high or low logic level. If LEAB is low, the A bus data is stored in the latch flip flop on the high to low transition of \overline{CLKAB} . Output enable OEAB is active high. When OEAB is high, the B port outputs are active. When OEAB is low, the B port outputs are in the high impedance state. Data flow for B to A is similar to that of A to B but uses \overline{OEBA} , LEBA, and \overline{CLKBA} . The output enables are complementary (OEAB is active high, and \overline{OEBA} is active low). Active bus hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

Features

- $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$
- Typical V_{OL} ground bounce < 0.8 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- Typical V_{OH} undershoot > 2.0 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- High output current ± 24 mA (@V_{CC} = 3.0 V)
- Bus hold on data inputs eliminates the need for external pullup / pulldown resistors



Function Table *3

Inputs	Output B				
OEAB	LEAB	CLKAB	Α		
L	X	Х	Х	Z	
Н	Н	X	L	L	
Н	Н	Χ	Н	Н	
Н	L	\downarrow	L	L	
Н	L	\downarrow	Н	Н	
Н	L	Н	Χ	B ₀ *1	
Н	L	L	X	B ₀ *2	

H: High level

L : Low level

X : Immaterial

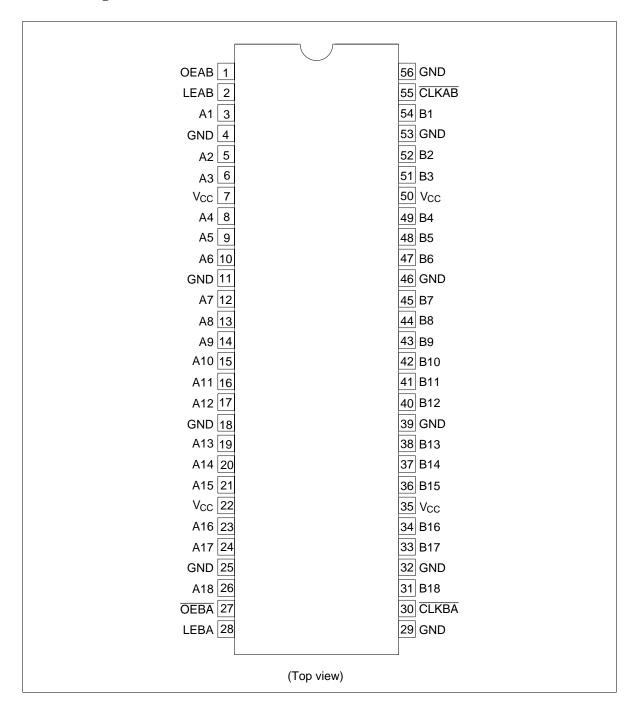
Z: High impedance

 \downarrow : High to low transition

Notes: 1. Output level before the indicated steady state input conditions were established.

- 2. Output level before the indicated steady state input conditions were established, provided that CLKAB was low before LEAB went low.
- 3. A to B data flow is show; B to A flow is similar but uses OEBA, LEBA, and CLKBA.

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{cc}	-0.5 to 4.6	V	_
Input voltage *1, 2	V _I	-0.5 to 4.6	V	Except I/O ports
		-0.5 to V_{cc} +0.5		I/O ports
Output voltage *1, 2	V _o	-0.5 to V _{cc} +0.5	V	
Input clamp current	I _{IK}	-50	mA	
Output clamp current	I _{OK}	±50	mA	$V_{o} < 0 \text{ or } V_{o} > V_{cc}$
Continuous output current	Io	±50	mA	$V_{\rm o}$ = 0 to $V_{\rm cc}$
		±100		
Maximum power dissipation at Ta = 55°C (in still air) ^{'3}	P _T	1	W	TSSOP
Storage temperature	Tstg	-65 to 150	°C	

Notes:

Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

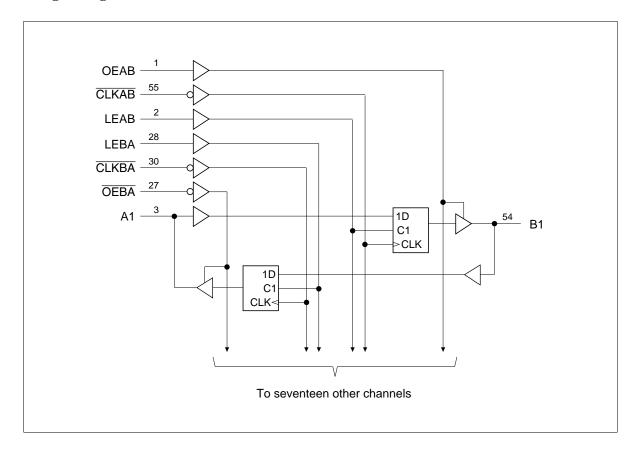
- 1. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.
- 2. This value is limited to 4.6 V maximum.
- 3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage	V _{cc}	2.3	3.6	V	
Input voltage	V _I	0	V _{cc}	V	
Output voltage	Vo	0	V _{cc}	V	
High level output current	I _{OH}	_	-12	mA	V _{CC} = 2.3 V
		_	-12		V _{CC} = 2.7 V
		_	-24		V _{CC} = 3.0 V
Low level output current	I _{OL}	_	12	mA	V _{CC} = 2.3 V
		_	12		V _{CC} = 2.7 V
		_	24		V _{CC} = 3.0 V
Input transition rise or fall rate	Δt / Δν	0	10	ns / V	
Operating temperature	Та	-40	85	°C	

Note: Unused control inputs must be held high or low to prevent them from floating.

Logic Diagram



Electrical Characteristics ($Ta = -40 \text{ to } 85^{\circ}\text{C}$)

Item	Symbol	V _{cc} (V) *1	Min	Max	Unit	Test Conditions
Input voltage	V _{IH}	2.3 to 2.7	1.7	_	V	
		2.7 to 3.6	2.0	_		
	V _{IL}	2.3 to 2.7	_	0.7		
		2.7 to 3.6	_	0.8		
Output voltage	V_{OH}	Min to Max	√ V _{CC} −0.2	_	V	$I_{OH} = -100 \mu A$
		2.3	2.0	_		$I_{OH} = -6 \text{ mA}, V_{IH} = 1.7 \text{ V}$
		2.3	1.7	_	_	$I_{OH} = -12 \text{ mA}, V_{IH} = 1.7 \text{ V}$
		2.7	2.2	_		$I_{OH} = -12 \text{ mA}, V_{IH} = 2.0 \text{ V}$
		3.0	2.4	_		$I_{OH} = -12 \text{ mA}, V_{IH} = 2.0 \text{ V}$
		3.0	2.0	_		$I_{OH} = -24 \text{ mA}, V_{IH} = 2.0 \text{ V}$
	V _{OL}	Min to Max	· —	0.2		I _{OL} = 100 μA
		2.3	_	0.4	<u> </u>	$I_{OL} = 6 \text{ mA}, V_{IL} = 0.7 \text{ V}$
		2.3	_	0.7	<u> </u>	$I_{OL} = 12 \text{ mA}, V_{IL} = 0.7 \text{ V}$
		2.7	_	0.4		$I_{OL} = 12 \text{ mA}, V_{IL} = 0.8 \text{ V}$
		3.0	_	0.55	<u> </u>	$I_{OL} = 24 \text{ mA}, V_{IL} = 0.8 \text{ V}$
Input current	I _{IN}	3.6	_	±5	μΑ	$V_{IN} = V_{CC}$ or GND
	I _{IN (hold)}	2.3	45	_	<u> </u>	$V_{IN} = 0.7 \text{ V}$
		2.3	-45	_		$V_{IN} = 1.7 V$
		3.0	75	_	<u> </u>	V _{IN} = 0.8 V
		3.0	-75	_		V _{IN} = 2.0 V
		3.6	_	±500		$V_{IN} = 0 \text{ to } 3.6 \text{ V}$
Off state output current	*2 I _{OZ}	3.6	_	±10	μΑ	$V_{OUT} = V_{CC}$ or GND
Quiescent supply curre	nt I _{cc}	3.6	_	40	μΑ	$V_{IN} = V_{CC}$ or GND
	ΔI_{cc}	3.0 to 3.6	_	750	μΑ	V_{IN} = one input at (V_{CC} -0.6) V, other inputs at V_{CC} or GND

Notes: 1. For conditions shown as Min or Max, use the appropriate values under recommended operating

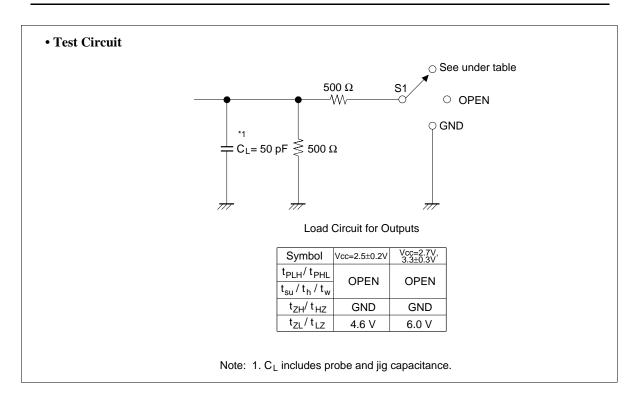
^{2.} For I/O ports, the parameter $\rm I_{\rm OZ}$ includes the input leakage current.

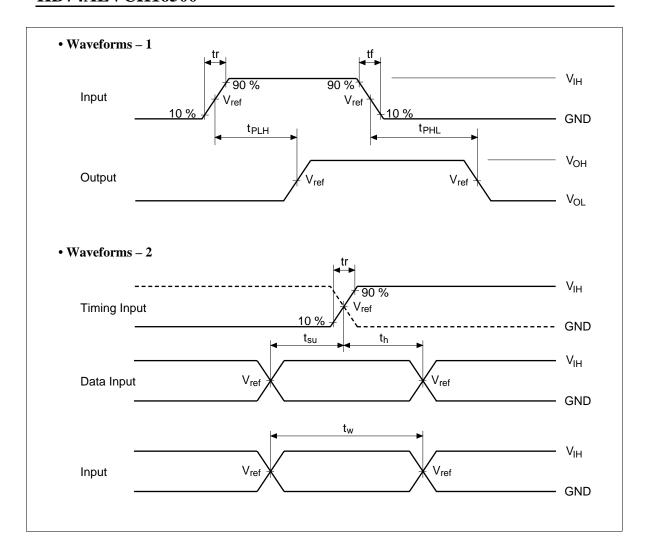
Switching Characteristics (Ta = -40 to 85° C)

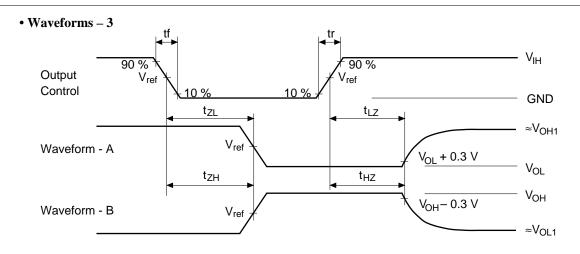
Item	Symbol	V _{cc} (V)	Min	Тур	Max	Unit	FROM (Input)	TO (Output)
Maximum clock frequency	f _{max}	2.5±0.2	150	_	_	MHz		
		2.7	150	_	_			
		3.3±0.3	150	_	_			
Propagation delay time	t_{PLH}	2.5±0.2	1.0	_	5.1	ns	A or B	B or A
	$t_{\tiny PHL}$	2.7	_	_	4.7			
		3.3±0.3	1.0	_	3.9			
		2.5±0.2	1.0	_	5.9		LEAB or	A or B
		2.7	_	_	5.5		LEBA	
		3.3±0.3	1.0	_	4.7	_		
		2.5±0.2	1.0	_	6.1		CLKAB or	A or B
		2.7	_	_	6.6		CLKBA	
		3.3±0.3	1.1	_	5.5	_		
Output enable time	t _{zH}	2.5±0.2	1.0	_	5.7	ns	OEAB	В
	$\mathbf{t}_{\scriptscriptstyle ZL}$	2.7	_	_	5.4	_		
		3.3±0.3	1.0	_	4.6	_		
		2.5±0.2	1.0	_	6.1		OEBA	Α
		2.7	_	_	6.2			
		3.3±0.3	1.0	_	5.2			
Output disable time	\mathbf{t}_{HZ}	2.5±0.2	1.7	_	6.2	ns	OEAB	В
	$t_{\scriptscriptstyle LZ}$	2.7	_	_	5.7			
		3.3±0.3	1.5	_	5.0	_		
		2.5±0.2	1.0	_	5.4		OEBA	Α
		2.7	_	_	4.6			
		3.3±0.3	1.0	_	4.3	_		
Input capacitance	C _{IN}	3.3	_	4.0	_	pF	Control inp	uts
Output capacitance	C _{IN/O}	3.3		8.0	_	pF	A or B port	s

Switching Characteristics (Ta = -40 to 85°C) (Cont)

Item	Symbol	V _{cc} (V)	Min	Тур	Max	Unit	FROM (Input)
Setup time	t _{su}	2.5±0.2	1.7	_	_	ns	Data before CLK↓
		2.7	1.4	_	_		
		3.3±0.3	1.3	_	_		
		2.5±0.2	1.1	_	_		Data before LE↓
		2.7	1.0	_	_		CLK "H"
		3.3±0.3	1.0	_	_		
		2.5±0.2	1.9	_	_		Data before LE↓
		2.7	1.6	_	_		CLK "L"
		3.3±0.3	1.4	_	_		
Hold time	t _h	2.5±0.2	1.7	_	_	ns	Data after $\overline{CLK} \!\downarrow$
		2.7	1.6	_	_		
		3.3±0.3	1.3	_	_		
		2.5±0.2	2.0	_	_		Data after LE↓
		2.7	1.8	_	_		CLK "H"
		3.3±0.3	1.5	_	_		
		2.5±0.2	1.6	_	_		Data after LE↓
		2.7	1.5	_	_		CLK "L"
		3.3±0.3	1.2	_	_		
Pulse width	t _w	2.5±0.2	3.3	_	_	ns	LE "H"
		2.7	3.3	_	_		
		3.3±0.3	3.3	_	_		
		2.5±0.2	3.3	_	_		CLK "H" or "L"
		2.7	3.3				
		3.3±0.3	3.3	_	_	_	







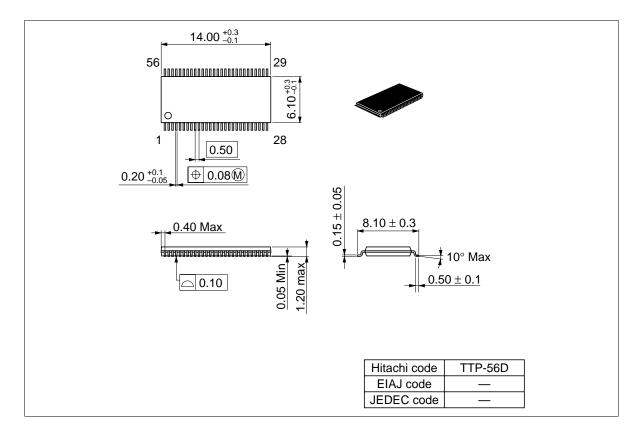
TEST	Vcc=2.5±0.2V	Vcc=2.7V, 3.3±0.3V
V_{IH}	2.3 V	2.7 V
V_{ref}	1.2 V	1.5 V
V _{OH1}	2.3 V	3.0 V
V _{OL1}	GND	GND

Notes: 1. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Zo = 50 Ω , tr \leq 2.5 ns, tf \leq 2.5 ns.

- 2. Waveform A is for an output with internal conditions such that the output is low except when disabled by the output control.
- 3. Waveform B is for an output with internal conditions such that the output is high except when disabled by the output control.
- 4. The output are measured one at a time with one transition per measurement.

Package Dimensions

Unit: mm



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